

## UNIVERSITI TUN HUSSEIN ONN MALAYSIA

# FINAL EXAMINATION **SEMESTER II SESSION 2012/2013**

COURSE NAME

: MATERIAL SCIENCE

COURSE CODE

: BNJ 10602

PROGRAMME

: 1 BNL/1BNK

**EXAMINATION DATE** : JUNE 2013

**DURATION** 

: 2 HOURS

INSTRUCTION

: 1. ANSWER FIVE (5) QUESTIONS ONLY FROM SIX (6) QUESTIONS PROVIDED

2. ATTACH FIGURE Q3, FIGURE Q4 (a) AND FIGURE Q4 (b) WITH YOUR

ANSWER BOOKLET

THIS QUESTIONS PAPER CONSISTS OF TEN (10) PAGES

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Q1 (a) By applying W. Pollack's formula, determine the distribution of electron in shell and subshell of Ti with atomic number 22.

(10 marks)

- (b) An x-ray diffractometer recorder chart for an element that has either the BCC or the FCC crystal structure showed diffraction peaks at the following  $2\theta$  angles:  $36.191^{\circ}$ ,  $51.794^{\circ}$ ,  $64.982^{\circ}$ , and  $76.663^{\circ}$  (The wavelength  $\lambda$  of the incoming radiation was 0.15405 nm). (Using **Table Q1 (a), Q1(b) and Q1(c)**, if necessary). Determine:
  - (i) The crystal structure of the element.
  - (ii) The lattice constant of the element and identify the element.

(10 marks)

Q2 Data molecular weights for a polyethylene material are tabulated in Table 1:

Table 1: Data molecular weight.

Molecular weight Range (g/mol)	Χi	Wi
15,000-30,000	0.04	0.01
30,000-45,000	0.07	0.04
45,000-60,000	0.16	0.11
60,000-75,000	0.26	0.24
75,000-90,000	0.24	0.27
90,000-105,000	0.12	0.16
105,000-120,000	0.08	0.12
120,000-135,000	0.03	0.15

Mer Structure of polyethylene is in **Figure Q2**, The atomic weight of C and H are 12.01 g/mol and 1.01 g/mol respectively.

#### Calculate:

(a) The number -average molecular weight.

(8 marks)

(b) The weight average molecular weight.

(8 marks)

(c) The degree of polymerization.

(4 marks)

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Q3		alloy of 80 wt% Sn-20 wt% Pb at the temperature of $200^{0}$ C (see <b>Figure</b> sity at $200^{0}$ C takes the densities of Pb and Sn to be $11.23$ and $7.24$ g/cm <sup>3</sup> respectively.	
	(a)	Describe what phase (s) is (are) present?	(2 marks)
	(b)	Determine the compositions of the phases?	(4 marks)
	(c)	Calculate the relative amount of each phase present in terms of mass fraction	on. (6 marks)
	(d)	Calculate the relative amount of each phase present in terms of volume fra	ction. (8 marks)
Q4	(a)	Plot the radial hardness profile (center, ½ R, ¾ R and surface) for diameter cylindrical specimen of 8640 steel that has been quenched in agitated water (Using data of Figure Q4 (a) and Q4 (b)). Please provyour answer with the Figure Q4 (a) and Q4 (b)).	moderately
			(12 marks)
	(b)	A 0.505 in. in diameter aluminium alloy test bar is subjected to a load of 2. If the diameter of the bar is 0.490 in. at this load, determine:	5,000 lb.
		(i) The engineering stress and strain.	
		(ii) The true stress and strain at this load.	
			(8 marks)

Q5 (a) Determine the elastic modulus of unidirectional epoxy-glass fiber composite in the longitudinal and transversal direction given the following data:  $E_{matrix} = 3.0 \text{ GPa}$ ,  $E_{fiber} = 70 \text{ GPa}$  and  $V_{fiber} = 0.6$ 

(6 marks)

(b) Calculate the reflectivity of ordinary light from a smooth, flat upper surface of a borosilicate (n=1.47) and polyethylene (n=1.53).

(5 marks)

(c) Using Table Q5, select the material for a conducting wire of diameter 40 mm that carries a current of 30 A and the maximum power dissipation is 5 W/m.

(5 marks)

- (d) The modulus of elasticity for titanium carbide (TiC) having 5 vol % porosity is 310 GPa. Calculate
  - (i) The modulus elasticity for non porous material.
  - (ii) The modulus of elasticity for 15% porosity.

(4 marks)

- Q6 (a) A silicon wafer is doped with 10<sup>21</sup> phosporus atoms/m<sup>3</sup>. Calculate:
  - (i) The majority carrier concentration
  - (ii) The minority -carrier concentration
  - (iii) The electrical resistivity of the doped silicon at room temperature (300 K). Assume complete inozation of the dopant atoms;  $n_i(Si) = 1.5 \times 10^{16} \text{ m}^{-3}$ ,  $\mu_n = 0.135 \text{ m}^2/\text{V.s}$ ), and  $\mu_p = 0.048 \text{ m}^2/\text{(V.s)}$

(10 marks)

(b) Calculate the number of silicon atoms per cubic meter. The density of silicon is 2.33 Mg/m<sup>3</sup> (2.33 g/cm<sup>3</sup>), and its atomic mass is 28.08 g/mol. Avogadro's number =6.023 x 10<sup>23</sup> atoms/mol.

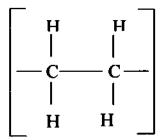
(4 marks)

- (c) A phosphorus-doped silicon wafer has an electrical resistivity of 8.33 x 10-5  $\Omega m$  at 27°C. Assume mobilities of charge carriers to be the constants 0.135 m<sup>2</sup>/(V.s) for electrons and 0.048 m<sup>2</sup>/(V.s) for holes.
  - (i) Calculate its majority-carrier concentration (carriers per cubic meter) if complete ionization is assumed?
  - (ii) Determine the ratio of phosphorus to silicon atoms in this material?

(6 marks)

#### END OF QUESTION -

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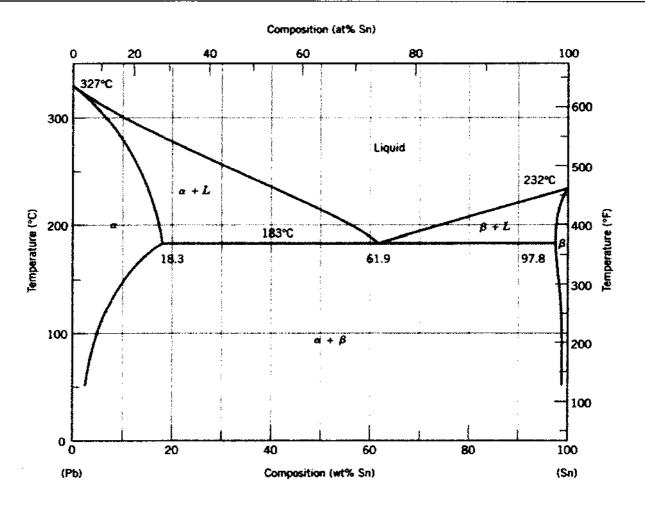
**FIGURE Q2** 

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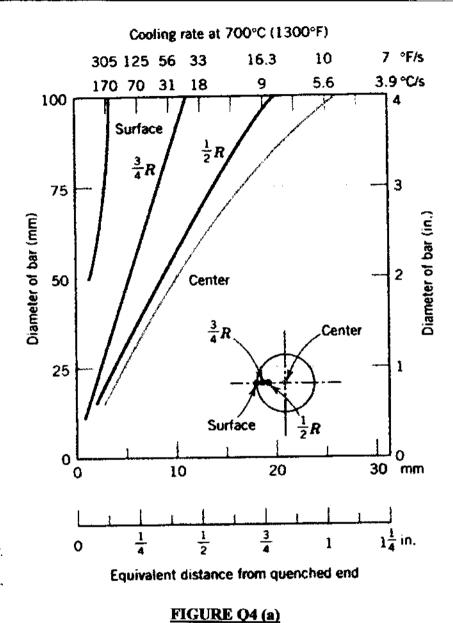
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## **FIGURE Q3**

SEMESTER/SESSION: SEM II/ 2012 2013 PROGRAMME : 1BNL/1BNK COURSE : MATERIAL SCIENCE COURSE CODE : BNJ10602



## **FINAL EXAMINATION** SEMESTER/SESSION: SEM II/ 2012 2013 PROGRAMME: 1BNL/1BNK : MATERIAL SCIENCE **COURSE** COURSE CODE: BNJ10602 Cooling rate at 700°C (1300°F) 3.5 °F/s 305 125 56 33 7 5.1 490 16.3 10 270 > 170 70 31 18 2 °C/s 5.6 3.9 2.8 60 - 100 4340 80 50 Hardness, HRC 50 4140 40 8640 30 5140 1040 20 10 20 30 40 50 mm $1\frac{1}{2}$ $1\frac{3}{4}$ $1\frac{1}{4}$ 1 2 in. 0 Distance from quenched end FIGURE Q4 (b)

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Table Q1 (a)
Miller indices of diffracting planes for BCC and FCC lattice

Cubic planes {hkl}	Cubic diffracting planes {hkl}	
	FCC	BCC
{100}		
{110}	***	110
{111}	111	
{200}	200	200
{210}		
{211}		211

Table Q1 (b)
Selected metals that have BCC crystal structure at room temperature (200°C) and their lattice constants

No.	Material	Lattice Constant a (nm)
1	Chromium	0.289
2	Iron	0.287
3	Molybdenum	0.315
4	Potassium	0.533
5	Sodium	0.429
6	Tungsten	0.316
7	Tantalum	0.338
8	Vanadium	0.304

Table Q1 (c)
Selected metals that have FCC crystal structure at room temperature (200°C) and their lattice constants

No.	Material	Lattice Constant a (nm)
1	Aluminium	0.405
2	Соррег	0.3615
3	Gold	0.408
4	Lead	0.495
5	Nickel	0.352
6	Platinum	0.393
7	Silver	0.409

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Table Q5
Electrical conductivities of some metals and non metals at room temperature

Metal and alloy	$\sigma(\Omega.m)^{-1}$	Non Metal	$\sigma (\Omega.m)^{-1}$
Silver	6.3 x 10 <sup>7</sup>	Graphite	10 <sup>5</sup>
Copper, commercial purity	5.8 x 10 <sup>7</sup>	Germanium	2.2
Gold	4.2 x 10 <sup>7</sup>	Silicon	4.3 x 10 <sup>-4</sup>
Aluminium, commercial purity	$3.4 \times 10^7$	Polyethylene	10 <sup>-4</sup>
		Polystyrene	10-4
		Diamond	10-4